

REMARKS

In paragraph 3 at pages 2-3 of the Office Action, claims 1-25 were rejected under 35 U.S.C. § 112, second paragraph, as being indefinite. Particularly, the Examiner questions how it is that the semiconductor layer precursor in the pores has a higher concentration than the semiconductor layer precursor in the electrolytic solution when energization occurs.

Applicants respond as follows.

The claims require the concentration of the precursor in the pores to be higher than the concentration of precursor in the electrolytic solution. This is accomplished by first dissolving precursor in a solvent (impregnating solution), impregnating the pores with the solvent containing the dissolved precursor before energization, and then dissipating (e.g., evaporating) the solvent to allow a large amount of monomer to remain in the pores (page 15, lines 4-9 and page 27, lines 11-16 of the specification). Next, the semiconductor layer is subsequently formed by energization in an electrolytic solution which also contains the precursor, whereby a semiconductor layer having a good impregnation ratio can be formed (page 15, lines 9-13 of the specification).

The solvents constituting the impregnating solution and the electrolytic solution may be the same, or they may be different.

For example, water containing precursor at a concentration of 1 % may be used both prior to energization and during energization. The pores are impregnated with the solution containing the dissolved precursor (1 %) before energization, and the water is then dissipated to allow a large amount of monomer to remain in the pores. Next, the semiconductor layer is subsequently formed by energization in an electrolytic solution containing the precursor in a concentration of 1

%, where the concentration of precursor in the pores (due to dissipation of the water) is higher than the concentration of precursor in the electrolytic solution.

As discussed above, the solvents may also be different, where, e.g., an alcohol solution containing precursor at a concentration of 1 % or 15 % is used prior to energization, and a water solution containing precursor at a concentration of 1 % is used during energization.

The effects of the invention can be achieved in all of these cases, as described at page 13, line 27 to page 14, line 20 of the specification. Further, as discussed at page 32, lines 9-18 of the specification and in reference to Table 1, when the pores are impregnated with the semiconductor layer-forming precursor before energization for forming the semiconductor layer and the concentration of semiconductor layer-forming precursor in the pores is rendered higher than the concentration of semiconductor layer-forming precursor in the electrolytic solution, a capacitor exhibiting a good capacitance appearance factor and a low ESR value can be obtained.

For the above reasons, it is respectfully submitted that the claims fully comply with 35 U.S.C. § 112, and withdrawal of the foregoing rejection is respectfully requested.

Withdrawal of all rejections and allowance of claims 1-25 is earnestly solicited.

In the event that the Examiner believes that it may be helpful to advance the prosecution of this application, the Examiner is invited to contact the undersigned at the local Washington, D.C. telephone number indicated below.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,



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